



CTLDM7002A-M621

SURFACE MOUNT
TINY LEADLESS MODULE™
ENHANCEMENT-MODE
N-CHANNEL MOSFET



TLM621 CASE

APPLICATIONS:

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage	V_{DS}	60	V
Drain-Gate Voltage	V_{DG}	60	V
Gate-Source Voltage	V_{GS}	40	V
Continuous Drain Current	I_D	280	mA
Continuous Source Current (Body Diode)	I_S	280	mA
Maximum Pulsed Drain Current	I_{DM}	1.5	A
Maximum Pulsed Source Current	I_{SM}	1.5	A
Power Dissipation (Note 1)	P_D	0.9	W
Operating and Storage Junction Temperature	T_J, T_{Stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance (Note 1)	Θ_{JA}	139	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{GSSF}	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$		100	nA
I_{GSSR}	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$		100	nA
I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$		1.0	μA
I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0\text{V}, T_J=125^\circ\text{C}$		500	μA
$I_{D(ON)}$	$V_{GS}=10\text{V}, V_{DS}\geq 2V_{DS(\text{ON})}$	500		mA
BV_{DSS}	$V_{GS}=0\text{V}, I_D=10\mu\text{A}$	60		V
$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	2.5	V
$V_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		1.0	V
$V_{DS(\text{ON})}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		0.15	V
V_{SD}	$V_{GS}=0\text{V}, I_S=400\text{mA}$		1.2	V

Notes: (1) FR-4 Epoxy PCB with copper mounting pad area of 33mm².**Central**™
Semiconductor Corp.**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CTLDM7002A-M621 is a Silicon N-Channel Enhancement-mode MOSFET in a small, thermally efficient, TLM™ 2x1mm package.

MARKING CODE: CP**FEATURES:**

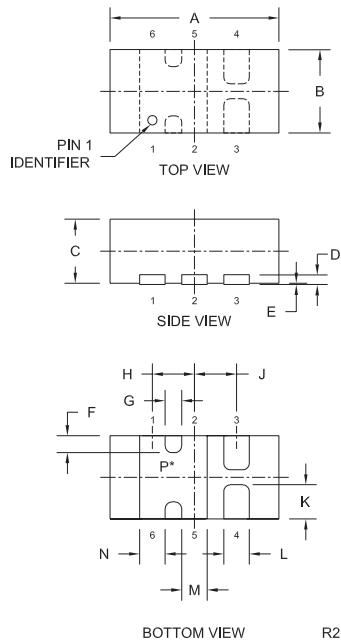
- Device is **Halogen Free** by design
- Low $R_{DS(\text{on})}$
- Low $V_{DS(\text{on})}$
- Low Threshold Voltage
- Fast Switching
- Logic Level Compatible
- Small TLM™ 2x1mm Package

SYMBOL**UNITS****V****A****W****°C****°C/W**

ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$r_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=500\text{mA}$	2.0	Ω	
$r_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=500\text{mA}$, $T_J=125^\circ\text{C}$	3.5	Ω	
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}$, $I_D=50\text{mA}$	3.0	Ω	
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}$, $I_D=50\text{mA}$, $T_J=125^\circ\text{C}$	5.0	Ω	
g_{FS}	$V_{DS} \geq 2V_{DS(ON)}$, $I_D=200\text{mA}$	80		mS
C_{rss}	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$	5.0	pF	
C_{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$	50	pF	
C_{oss}	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$	15	pF	
t_{on}	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=200\text{mA}$	20		ns
t_{off}	$R_G=25\Omega$, $R_L=150\Omega$	20		ns

TLM621 CASE - MECHANICAL OUTLINE

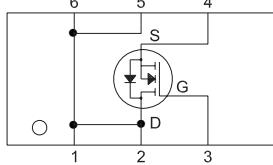


*Exposed pad P connects pins 1, 2, 5, and 6

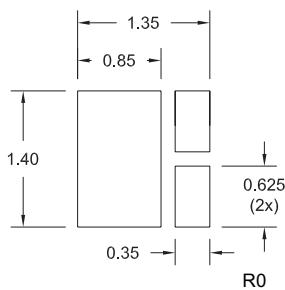
SYMBOL	DIMENSIONS		INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX	MIN	MAX
A	0.073	0.085	1.850	2.150		
B	0.033	0.045	0.850	1.150		
C	0.028	0.031	0.700	0.800		
D	0.006		0.150			
E	0.000	0.002	0.000	0.050		
F	0.008		0.200			
G	0.010		0.250			
H	0.020		0.500			
J	0.020		0.500			
K	0.012	0.020	0.300	0.500		
L	0.007	0.012	0.180	0.300		
M	0.007	0.012	0.180	0.300		
N	0.007	0.012	0.180	0.300		

TLM621 (REV: R2)

PIN CONFIGURATION



SUGGESTED MOUNTING PADS
(Dimensions in mm)



LEAD CODE:

- 1) DRAIN
- 2) DRAIN
- 3) GATE
- 4) SOURCE
- 5) DRAIN
- 6) DRAIN

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